

N-channel TrenchMOS standard level FET

13 July 2012

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	75	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	137	W
Static char	acteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 20 A; T _j = 25 °C; Fig. 11		-	5.9	8.3	mΩ
Dynamic cl	naracteristics	·			_		
Q_{GD}	gate-drain charge	I _D = 20 A; V _{DS} = 48 V; V _{GS} = 10 V; Fig. 14		-	14.6	-	nC

[1] Continuous current is limited by package.

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UTA
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

3. Ordering information

Table 3. Ordering inf	formation		
Type number	Package		
	Name	Description	Version
BUK768R3-60E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	60	V
V _{GS}	gate-source voltage	T _j = 25 °C		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	75	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>		-	61.5	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	349	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	137	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	75	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	349	А

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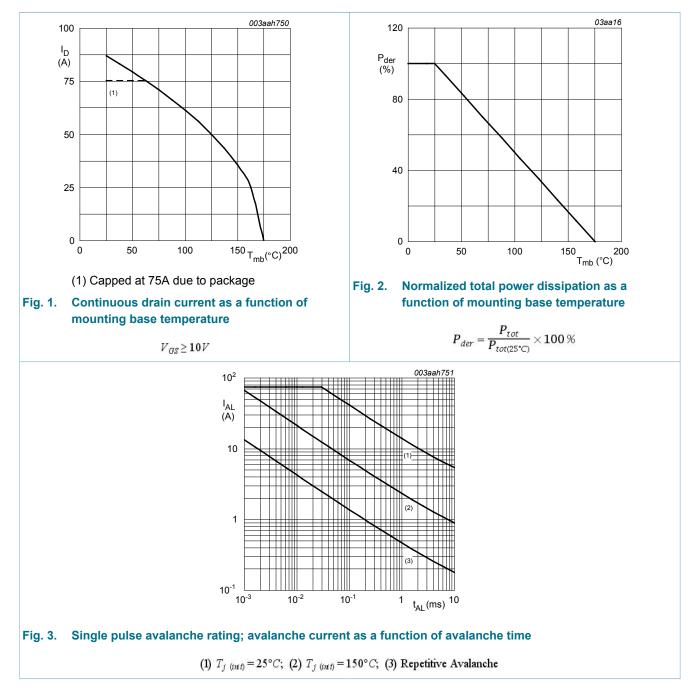
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Symbol	Parameter	Conditions		Min	Мах	Unit
Avalanche rug	gedness					-
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 75 \text{ A}; \text{V}_{\text{sup}} \leq 60 \text{V}; \text{R}_{\text{GS}} = 50 \Omega; \\ \text{V}_{\text{GS}} &= 60 \text{V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 3} \end{split}$	[<u>2][3]</u>	-	86	mJ

[1]

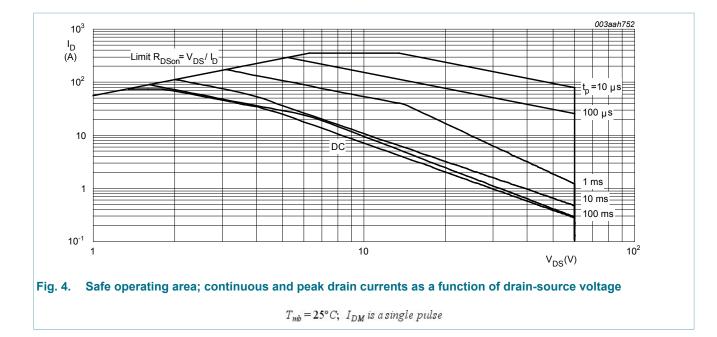
Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [2]

[3] Refer to application note AN10273 for further information.



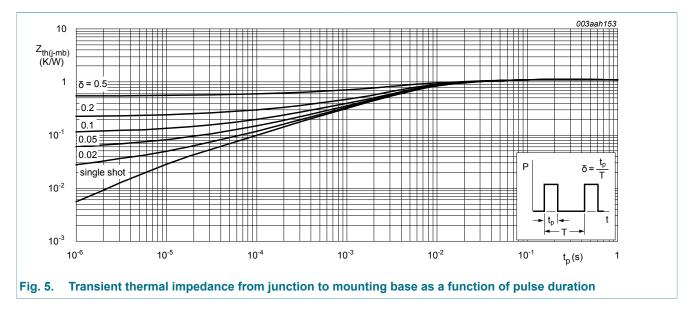
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5. Thermal characteristics

Table 5. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	1.09	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W



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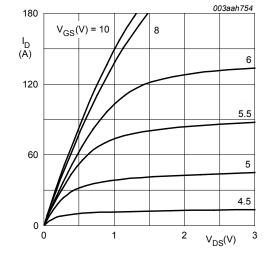
6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics	1				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	54	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 9	1	-	-	V
		$I_D = 1 \text{ mA; } V_{DS} = V_{GS}; T_j = -55 \text{ °C;}$ Fig. 9	-	-	4.5	V
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.04	1	μA
		V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 20 A; T _j = 25 °C; Fig. 11	-	5.9	8.3	mΩ
		V _{GS} = 10 V; I _D = 20 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	18	mΩ
Dynamic cl	naracteristics					
Q _{G(tot)}	total gate charge	I _D = 20 A; V _{DS} = 48 V; V _{GS} = 10 V; Fig. 13; Fig. 14	-	43.1	-	nC
Q _{GS}	gate-source charge	I_D = 20 A; V_{DS} = 48 V; V_{GS} = 10 V;	-	10.9	-	nC
Q _{GD}	gate-drain charge	Fig. 14	-	14.6	-	nC
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;	-	2188	2920	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	319	383	pF
C _{rss}	reverse transfer capacitance		-	205	281	pF
t _{d(on)}	turn-on delay time	V_{DS} = 45 V; R_L = 2 Ω ; V_{GS} = 10 V;	-	14	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	27	-	ns
t _{d(off)}	turn-off delay time		-	27	-	ns
t _f	fall time		-	27	-	ns
L _D	internal drain inductance	from upper edge of mounting base to centre of die	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad	-	7.5	-	nH

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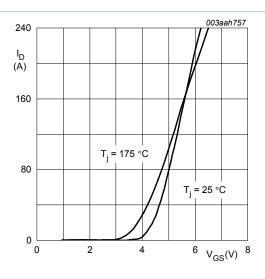
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain	liode					
V _{SD}	source-drain voltage	I_{S} = 20 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.84	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V_{\rm GS} = 0 V;	-	27	-	ns
Q _r	recovered charge	V _{DS} = 25 V	-	24	-	nC



T_j = 25 °C; t_p = 300 μs







 $V_{DS} = 10V$

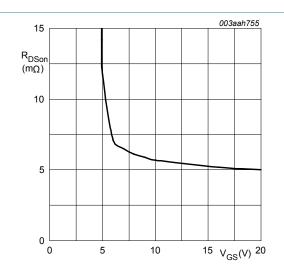
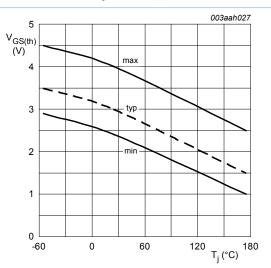


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 20^{\circ}C; I_D = 20A$

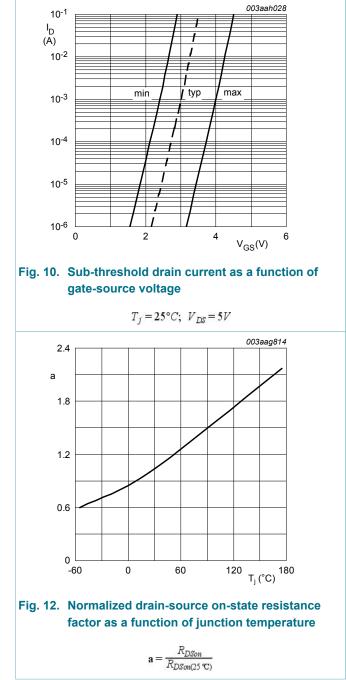


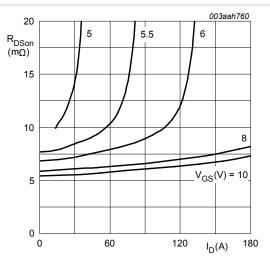


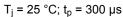
 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

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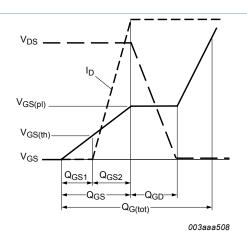
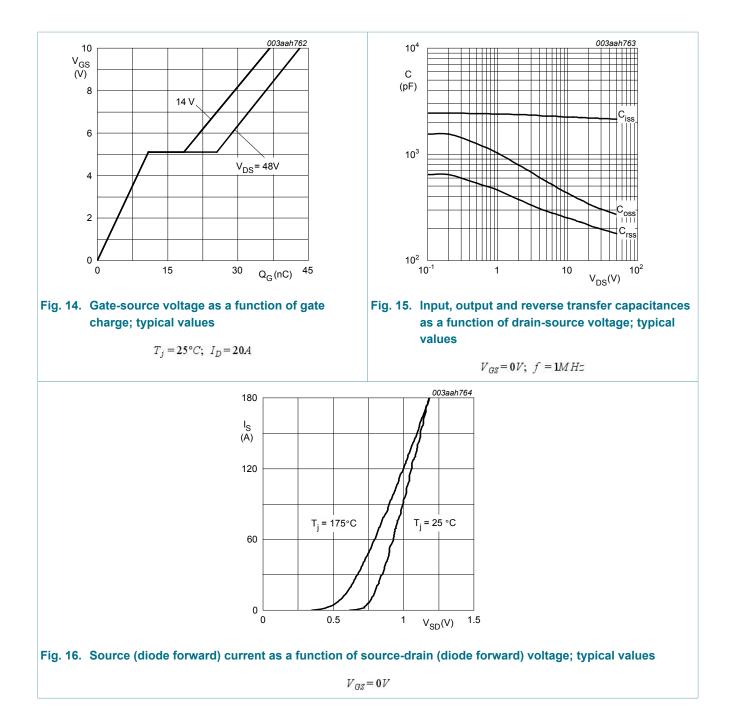


Fig. 13. Gate charge waveform definitions

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7. Package outline

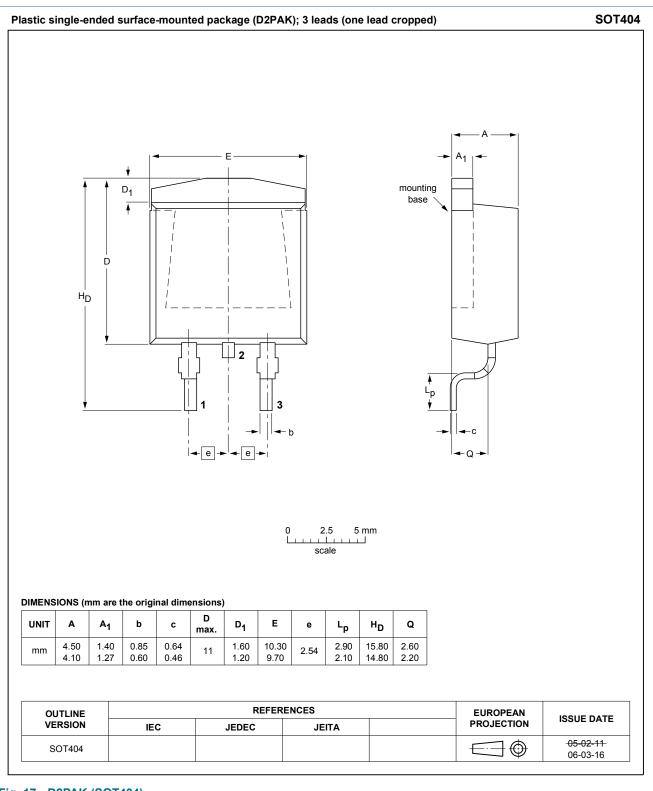


Fig. 17. D2PAK (SOT404)

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